

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Katsunobu HORI, et al.

Serial No.: 09/756,846

Filed: January 10, 2001

For: SEMICONDUCTOR DEVICE HAVING A LAYERED WIRING STRUCTURE WITH HARD MASK COVERING (AS AMENDED)

Group Art Unit: 2811

Examiner: H. Vu

THE COMMISSIONER FOR PATENTS AND TRADEMARKS
Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

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No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	7	20	0	\$18.00 =	\$0.00
Independent Claims	2	3	0	\$84.00 =	\$0.00
Multiple claims newly presented					\$0.00
Fee for extension of time					\$0.00
					\$0.00
Total of Above Calculations					\$0.00

☐
Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.
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The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Scott D. Paul

Registration No. 42,984

600 13th Street, N.W.
 Washington, DC 20005-3096
 (202) 756-8000 SDP:cac
 Facsimile: (202) 756-8087
 Date: October 29, 2002



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Docket No.: 50090-270



PATENT

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HARD MASK COVERING (AS AMENDED)

AMENDMENT

Box Non-Fee Amendment
The Commissioner for Patents and Trademarks
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action
dated August 2, 2002. Please amend the above-identified application as follows:

IN THE TITLE:

Please replace "SEMICONDUCTOR DEVICE HAVING A LAYERED WIRING
STRUCTURE" with "--SEMICONDUCTOR DEVICE HAVING A LAYERED WIRING
STRUCTURE WITH HARD MASK COVERING--".

IN THE SPECIFICATION:

Page 21, first paragraph, please delete in its entirety and replace with the following:

--in the first etching. In the practice of the invention, it is permitted to form the anti-reflective
film on the surface of a thin film material, i.e. on the surface of the metal material made thin in

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